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3. Nature of Conveyance:				u.
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Execution Date:July 8, 2003				
 Application number(s) or patent number(s): 	106271	LU		
If this document is being filed together wit	h a new application,	the execution date of the appl	ication is: <u>July 22, 200</u>	3
If this document is being filed together wit A. Patent Application No.(s) –	h a new application,	the execution date of the appl B. Patent No.(s)	ication is: <u>July 22, 200</u>	3
	Nonvolatile Memories	B. Patent No.(s)	ication is: <u>July 22, 200</u>	3
A. Patent Application No.(s) – Title: Fabrication of Gate Dielectric In N	Nonvolatile Memories	B. Patent No.(s)	ication is: <u>July 22, 200</u> Yes X No	
A. Patent Application No.(s) – Title: Fabrication of Gate Dielectric In N n Which A Memory Cell Has Multiple Floating Gate	Nonvolatile Memories es Additional nu	B. Patent No.(s)	Yes 🔀 No)
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 A. Patent Application No.(s) – Title: Fabrication of Gate Dielectric In No. Multiple: Floating Gate Name and address of party to whom correspondence on concerning document should be mailed: Name: Michael Shenker 	Nonvolatile Memories es Additional nu dence	B. Patent No.(s)	Yes 🔀 No)
 A. Patent Application No.(s) – Title: Fabrication of Gate Dielectric In N in Which A Memory Cell Has Multiple Floating Gate Name and address of party to whom correspond concerning document should be mailed: Name: <u>Michael Shenker</u> Internal Address: <u>MACPHERSON, KWOK CHEN</u> 	Nonvolatile Memories Additional nu dence	B. Patent No.(s) mbers attached?	Yes X No)
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ASSIGNMENT

For good and valuable consideration, receipt of which is hereby acknowledged, I,

Yi Ding of Sunnyvale, California

hereby sell, assign and transfer to Mosel Vitelic, Inc. a Taiwan corporation, having a place of business at No. 19 Li Hsin Road, Science Based Industrial Park, Hsin Chu City, Taiwan its successors and assigns, the entire right, title and interest throughout the world in our invention in

Fabrication of Gate Dielectric In Nonvolatile Memories in Which A Memory Cell Has **Multiple** Floating Gates

for which I have executed a United States patent application on or about the date of this assignment, and all patent applications and patents of every country for said invention, including divisions, reissues, continuations and extensions thereof, and all rights of priority resulting from the filing of said applications; we authorize the above-named assignee to apply for patents of foreign countries for said invention, and to claim all rights of priority without further authorization from us; we agree to execute all papers useful in connection with said United States and foreign applications, and generally to do everything possible to aid said assignee, their successors, assigns and nominees, at their request and expense, in obtaining and enforcing patents for said invention in all countries; and we request that the United States Patent and Trademark Office issue all patents granted for said invention to the above-named assignee, its successors and assigns.

Executed this <u>8</u> day of <u>July</u> 2003. State of <u>Colifornic</u>) Santa) ss County of <u>Clare</u>)

On $\frac{0.7/08/2003}{1000}$ 2003, before me, <u>Norman</u> Piking personally appeared to me on the basis of satisfactory evidence to be the person(s) whose name(s) is(are) subscribed to the within instrument and acknowledged to me that he/she/they executed the same in his/her/their authorized capacity(ies), and that by his/her/their signature(s) on the instrument the person(s), or the entity upon behalf of which the person(s) acted, executed the instrument.



WITNESS my hand and official seal.

Nowa Pitater Signature of NOTARY